

Docket No. 240800US-2S DIV  
 IN RE APPLICATION OF: Norihisa ARAI  
 SERIAL NO: 10/670,529  
 FILED: SEPTEMBER 26, 2003  
 FOR: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING PROCESS FOR IMPLANTING  
 IMPURITIES INTO SUBSTRATE VIA MOS TRANSISTOR GATE ELECTRODE AND GATE INSULATION  
 FILM



COMMISSIONER FOR PATENTS  
 ALEXANDRIA, VIRGINIA 22313

SIR:  
 Transmitted herewith is an amendment in the above-identified application.

- ☒ No additional fee is required  
☐ Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.  
☐ Additional documents filed herewith:

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	15	MINUS	20	0	x \$18 =	\$0.00
INDEPENDENT	3	MINUS	3	0	x \$86 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+ \$290 =	\$0.00
		TOTAL OF ABOVE CALCULATIONS				\$0.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment			+ \$40 =	\$0.00
		TOTAL				\$0.00

- ☐ A check in the amount of **\$0.00** is attached.  
☐ Credit card payment form is attached to cover the fees in the amount of **\$0.00**  
☒ Please charge any additional Fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.  
☒ If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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DOCKET NO: 240800US-2S DIV



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
NORIHISA ARAI : ATTN: APPLICATION DIVISION  
SERIAL NO: 10/670,529 :  
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SUPPLEMENTAL PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Supplemental to the preliminary amendment filed on September 26, 2003, please  
amend this application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on  
page 2 of this paper.

**Remarks/Arguments** begin on page 6 of this paper.